



SIHG25N50E-GE3 Information



For Reference Only

Part Number SIHG25N50E-GE3 **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 26A TO-247AC

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SIHG25N50E-GE3 Specifications

Manufacturer Part Number SIHG25N50E-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 26A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 86nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1980pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 250W (Tc) Rds On (Max) @ Id, Vgs 145 mOhm @ 12A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AC Package / Case TO-247AC		
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Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C26A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs86nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1980pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs145 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ACPackage / CaseTO-247-3		Transistors - FETs, MOSFETs - Single
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Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 26A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 145 mOhm @ 12A, 10V Operating Temperature - Supplier Device Package TO-247AC Package / Case TO-247-3	Series	-
Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C26A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs86nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1980pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs145 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ACPackage / CaseTO-247-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 145 mOhm @ 12A, 10V Operating Temperature Supplier Device Package TO-247AC Package / Case 26A (Tc) 270	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Rome Capacitance (Ciss) (Max) @ Vds Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 145 mOhm @ 12A, 10V Operating Temperature Coperating Type Through Hole Supplier Device Package TO-247AC Package / Case TO-247-3	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	26A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1980pF @ 100V Vgs (Max) ±30V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 145 mOhm @ 12A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AC Package / Case TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 145 mOhm @ 12A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AC Package / Case TO-247-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs145 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ACPackage / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	86nC @ 10V
FET Feature - Case - Ca	Input Capacitance (Ciss) (Max) @ Vds	1980pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 145 mOhm @ 12A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AC Package / Case TO-247-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs145 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ACPackage / CaseTO-247-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AC Package / Case TO-247-3	Power Dissipation (Max)	250W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247AC Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	145 mOhm @ 12A, 10V
Supplier Device Package TO-247AC Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247AC
Report errors?	Package / Case	TO-247-3
		Report errors?

SIHG25N50E-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SIHG25N50E-GE3 Payment Methods



















SIHG25N50E-GE3 Shipping Methods













If you have any question about SIHG25N50E-GE3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com